

## EE204: HW 1

1)

(a)

Code:

\*Ids-Vds and Ids-Vgs of a n-MOSFET

.include tsmc.txt

M1 2 1 0 0 CMOSN W=10u

VDD 2 0 DC 5v

VGG 1 0 DC 2.5V

\*defining the run-time control functions

.dc VGG 0 5 0.05

\*VDD 0 5 5

\*.dc VDD 0 10 0.05

.control

run

\*plotting input and output voltages

\*plot -I(vdd)

plot deriv(-I(vdd))

\*plot I(vgg) vs v(1)

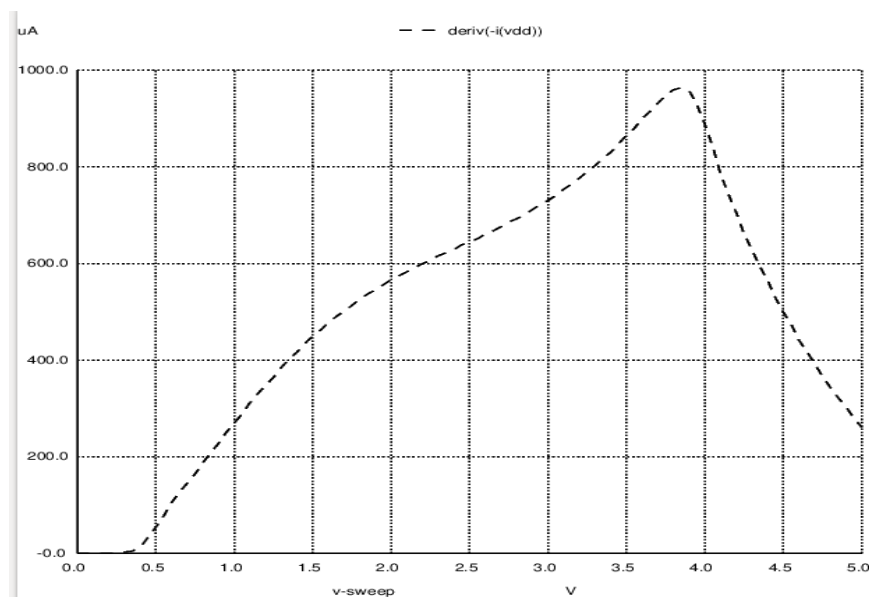
hardcopy q1 deriv(-I(vdd))

wrdata q2 deriv(-I(vdd))

.endc

.end

Plot:



The value of maximum transconductance = 963.45uS

(b) The maxima occurs at  $V_{gs} = 3.85V$ .

Data points:

3.70000000e+00	9.31865918e-04
3.75000000e+00	9.47004724e-04
3.80000000e+00	9.58682182e-04
3.85000000e+00	9.63450498e-04
3.90000000e+00	9.55889418e-04
3.95000000e+00	9.30598946e-04
4.00000000e+00	8.88297865e-04

(c) Code:

\*Ids-Vds and Ids-Vgs of a n-MOSFET

.include tsmc.txt

M1 2 1 0 0 CMOSN W=10u

VDD 2 0 DC 5v

VGG 1 0 DC 3.85V

\*defining the run-time control functions

\*.dc VGG 0 5 0.05

\*VDD 0 5 5

.dc VDD 0 10 0.05

.control

run

\*plotting input and output voltages

\*plot -I(vdd)

plot deriv(-I(vdd))

\*plot I(vgg) vs v(1)

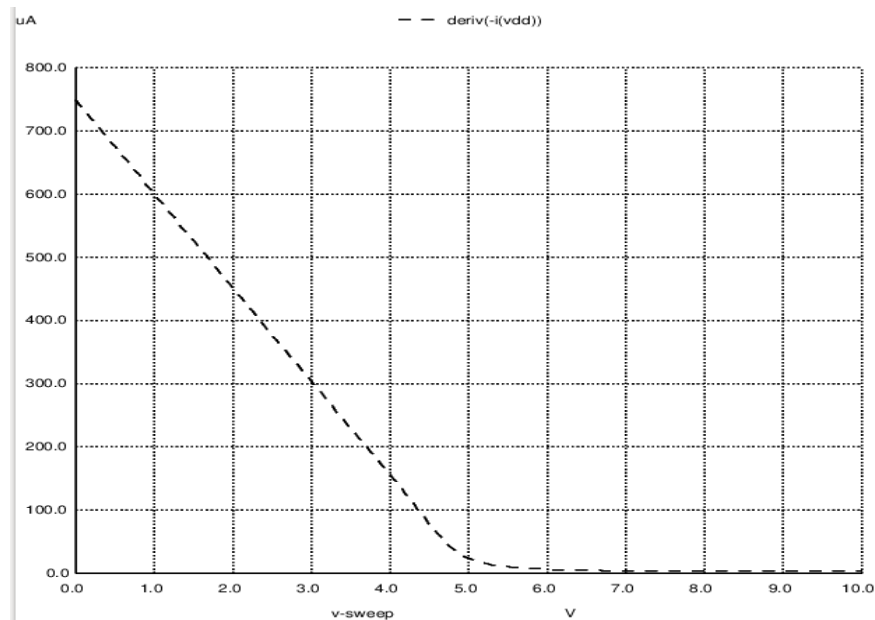
hardcopy q1 deriv(-I(vdd))

wrdata q2 deriv(-I(vdd))

.endc

.end

Plot:

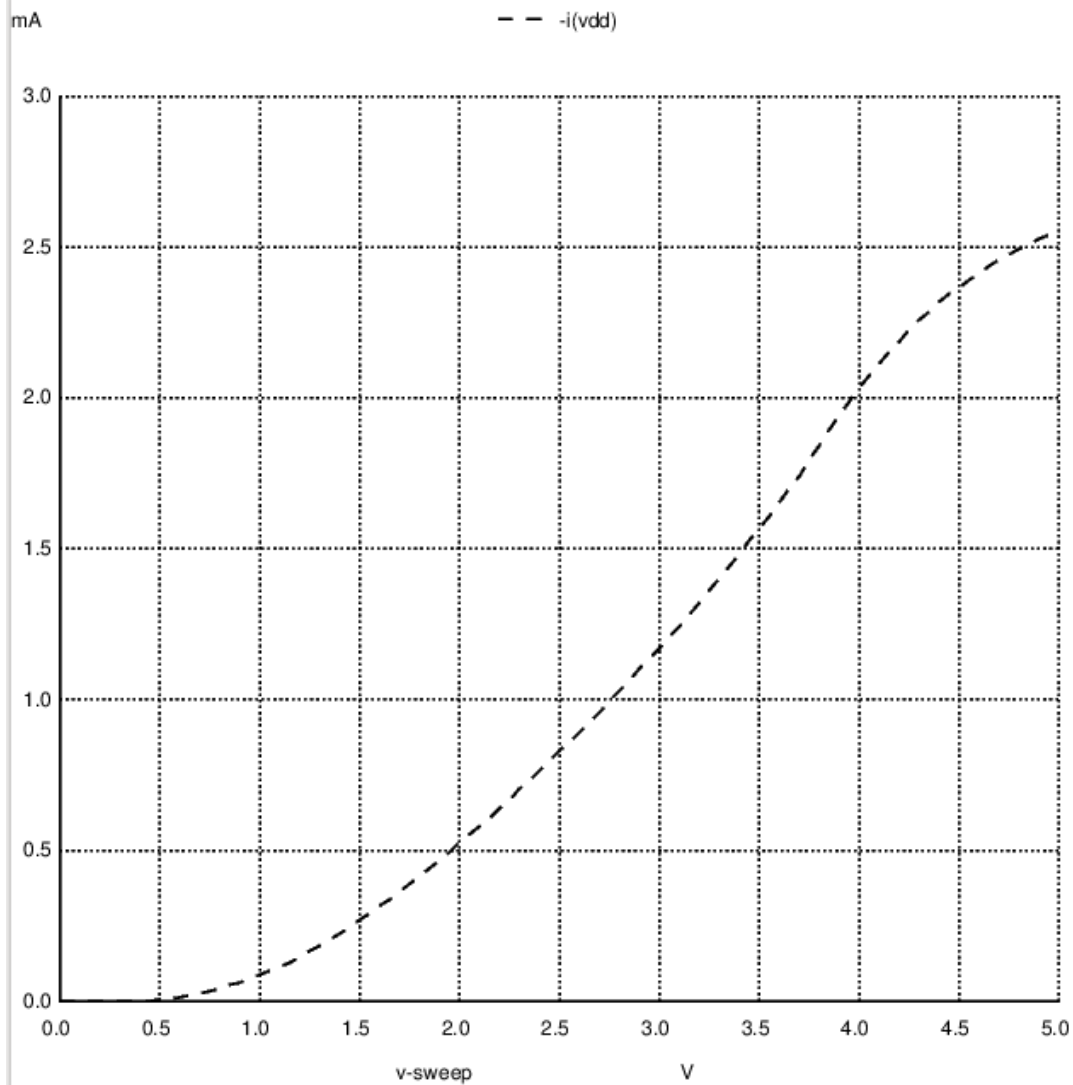


Datapoints:

4.85000000e+00	3.35358530e-05
4.90000000e+00	2.96271736e-05
4.95000000e+00	2.62861055e-05
5.00000000e+00	2.34398827e-05
5.05000000e+00	2.10170516e-05
5.10000000e+00	1.89521737e-05
5.15000000e+00	1.71878491e-05

At  $V_{ds}=5$ ,  $1/r_o = 2.344e-5$ , Thus, the intrinsic output resistance ( $r_o$ ) = 42.66kohm

## Transfer Characteristics of MOSFET:



The  $V_t$  observed here is 0.5V.

Q2.

(a) code:

\*Ids-Vds and Ids-Vgs of a n-MOSFET

```
.include tsmc.txt
```

```
M1 2 1 0 0 CMOSN W=10u
```

```
VDD 3 0 dc 15v
```

```
Vgg 4 0 dc 2.1v
```

```
Rd 2 3 19k
```

```
Vin 1 4 ac sin(0 100m 1k 0 0)
```

```
.tran 0.02m 10m
```

```
.control
```

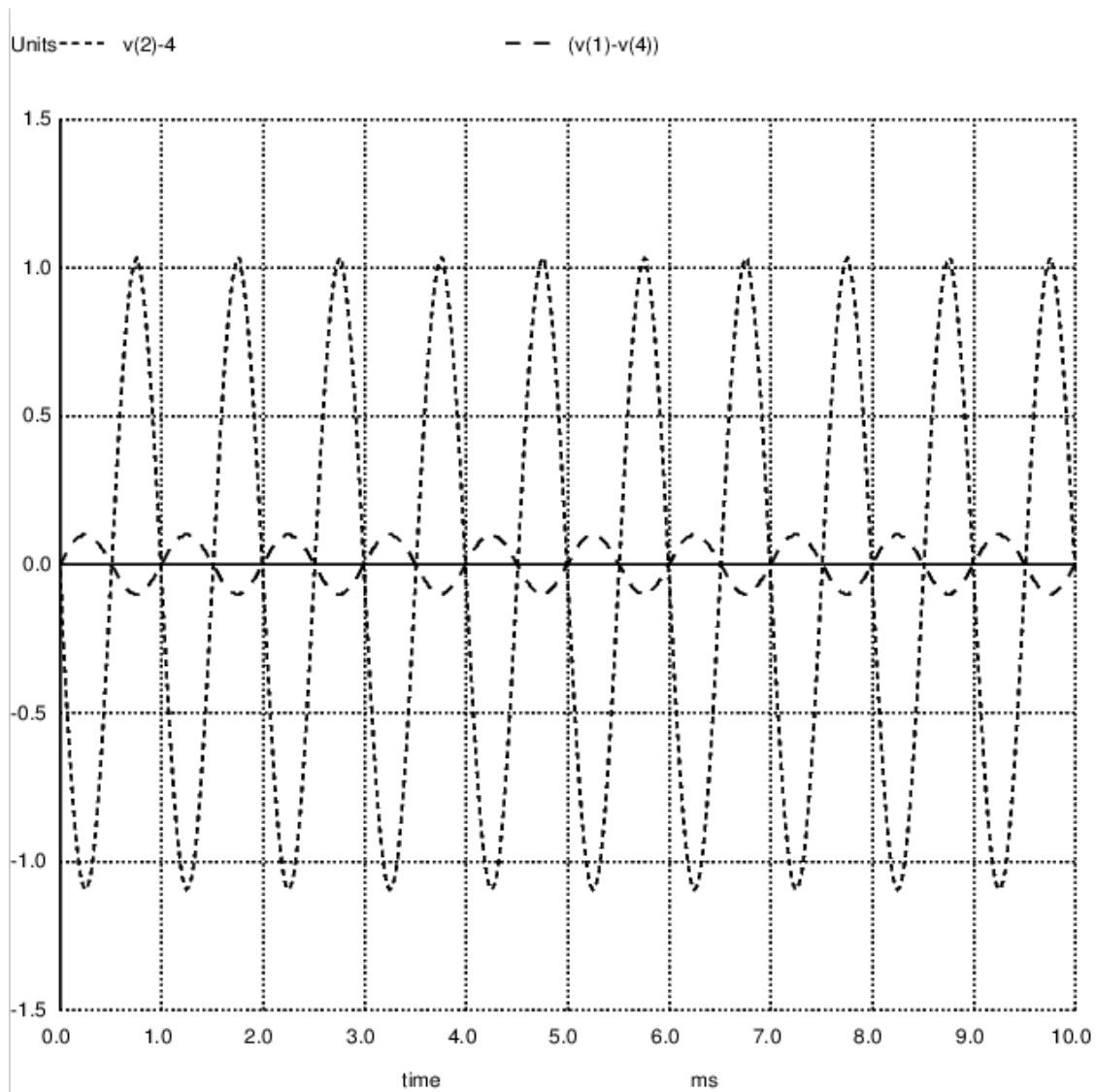
```
run
```

```
plot (v(1)-v(4)), v(2)-4
```

```
hardcopy q1 (v(1)-v(4)), v(2)-4
```

```
.endc
```

```
.end
```



(b) Code:

\*Ids-Vds and Ids-Vgs of a n-MOSFET

```
.include tsmc.txt
```

```
M1 2 1 3 0 CMOSN W=10u
```

```
VDD 2 0 dc 15v
```

```
Vgg 4 0 dc 14.9v
```

```
Rs 3 0 29.12k
```

```
Vin 1 4 ac sin(0 0.1 0.5k 0 0)
```

```
.tran 0.02m 10m
```

```
.control
```

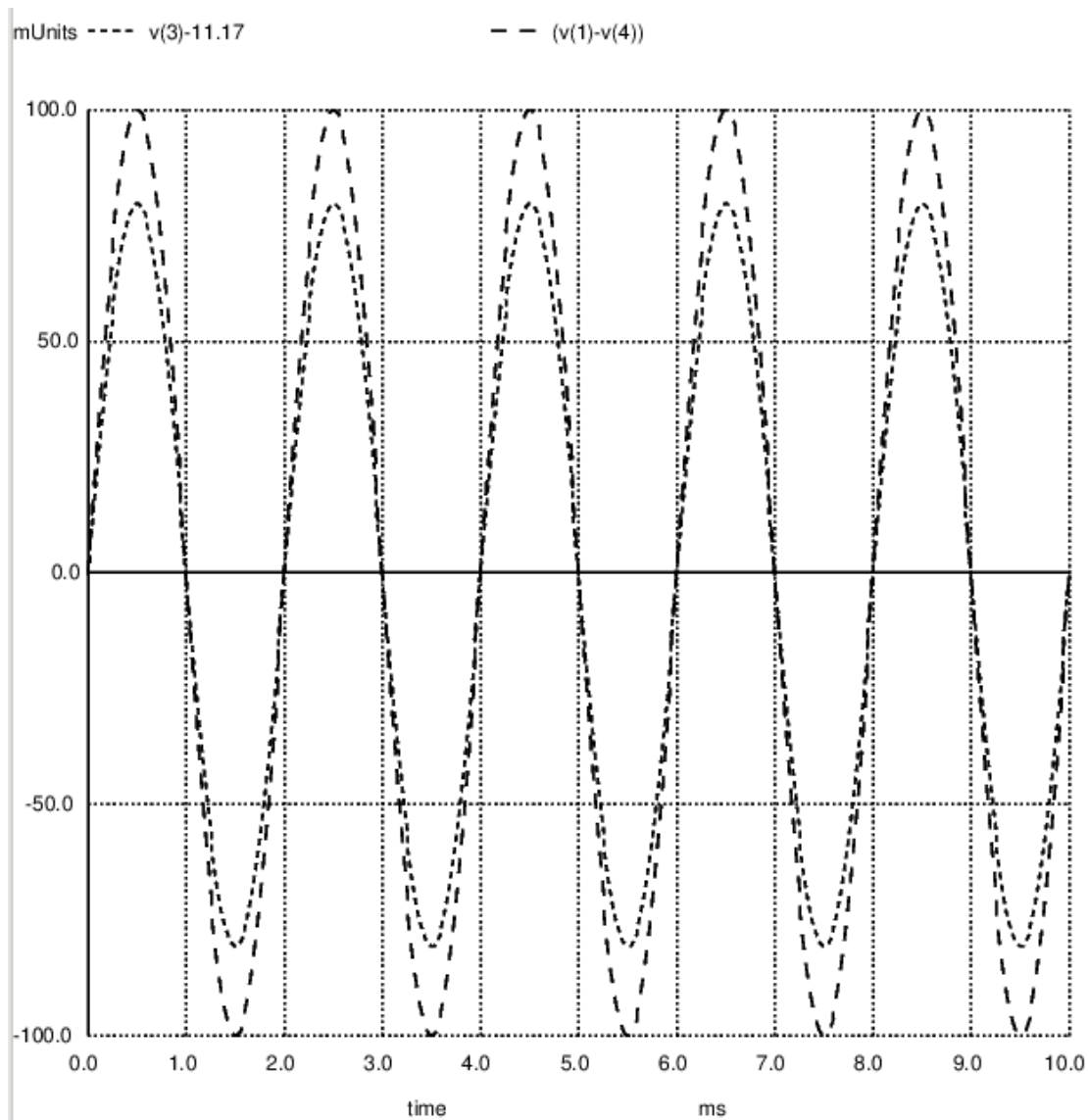
```
run
```

```
plot (v(1)-v(4)), v(3)-11.17
```

```
hardcopy q1 (v(1)-v(4)), v(3)-11.17
```

```
.endc
```

```
.end
```



(c) Code:

\*Ids-Vds and Ids-Vgs of a n-MOSFET

.include tsmc.txt

M1 2 1 3 0 CMOSN W=10u

VDD 4 0 dc 15v

Vgg 1 0 dc 2.3v

Rd 4 2 3k

Rs 3 5 1.9k

Vin 5 0 ac sin(0 0.1 0.5k 0 0)

.tran 0.02m 10m

.control

run

plot v(5), v(2)-14.085

hardcopy q1 v(5), v(2)-14.085

.endc

.end

mUnits ---- v(2)-14.085

- - - v(5)

